

DESCRIPTIVE ABSTRACT

This is a phase-change memory cell
5 including between two electrical contacts (1, 2), a
portion (3) in a memory material with amorphous-
crystalline phase-change and vice versa, as a stack
with a central area (3.1) located between two outmost
areas (3.2, 3.3). An interface (3.21, 3.31), inert or
10 quasi-inert from a physico-chemical point of view, is
present between the so-called active central area (3.1)
and each so-called passive outmost area (3.2, 3.3).
Each passive outmost area (3.2, 3.3) is made in a
material having a melting temperature higher than that
15 of the material of the active central area (3.1).

Notably applied to PC RAM memories.

Fig. 1A.